## 2SA2102

## Silicon PNP epitaxial planar type

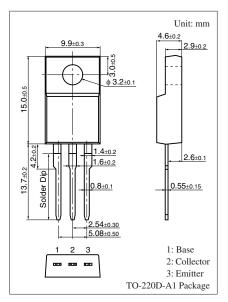
Power supply for Audio & Visual equipments such as TVs and VCRs
Industrial equipments such as DC-DC converters

#### ■ Features

- ullet High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- Superior forward current transfer ratio h<sub>FE</sub> linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

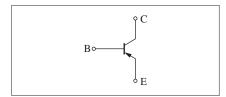
### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit		
Collector-base voltage (Emitter open)		$V_{CBO}$	-60	V	
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	-60	V	
Emitter-base voltage (Collector open)		$V_{EBO}$	-6	V	
Collector current		$I_{C}$	-3	A	
Peak collector current		$I_{CP}$	-5	A	
Collector power	$T_C = 25^{\circ}C$	P <sub>C</sub>	15	W	
dissipation	$T_a = 25$ °C		2		
Junction temperature	T <sub>j</sub>	150	°C		
Storage temperature	T <sub>stg</sub>	-55 to +150	°C		



Marking Symbol: A2102

#### Internal Connection



#### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -10 \text{ mA}, I_B = 0$	-60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -60 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -0.2 \text{ A}$	60			_
	h <sub>FE2</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	80		250	_
	h <sub>FE3</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$	30			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -3 \text{ A}, I_B = -0.375 \text{ A}$			- 0.8	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = -0.1 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Turn-on time	t <sub>on</sub>	$I_C = -1$ A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		0.4		μs
Fall time	$t_{\rm f}$	$V_{CC} = -50 \text{ V}$		0.1		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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